



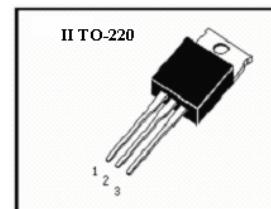
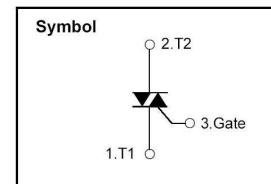
Shantou Huashan Electronic Devices Co.,Ltd.

HBTA12A60**INNER INSULATED TYPE TRIAC (II T0-220 PACKAGE)****Features**

- * Repetitive Peak Off-State Voltage: 600V
- * R.M.S On-state Current($I_{T(RMS)}=12A$)
- * High Commutation dv/dt

General Description

The Triac HBTA8A60 is suitable for AC switching application, phase control application such as heater control, motor control, lighting control, and static switching relay.

**Absolute Maximum Ratings ($T_a=25^\circ C$)**

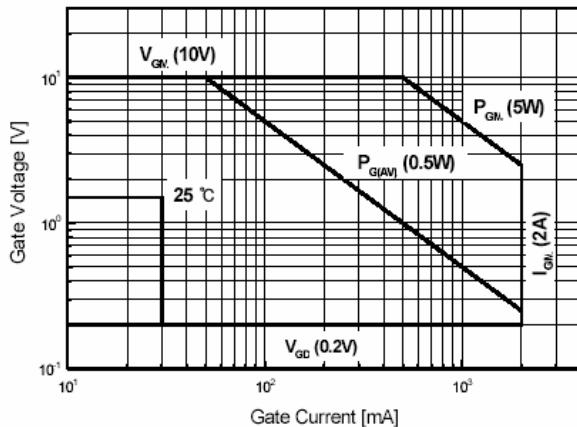
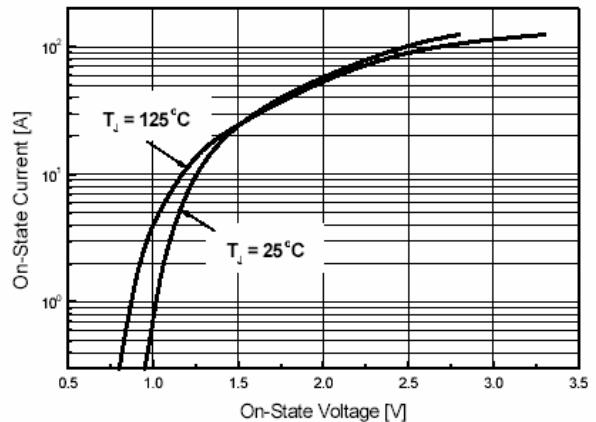
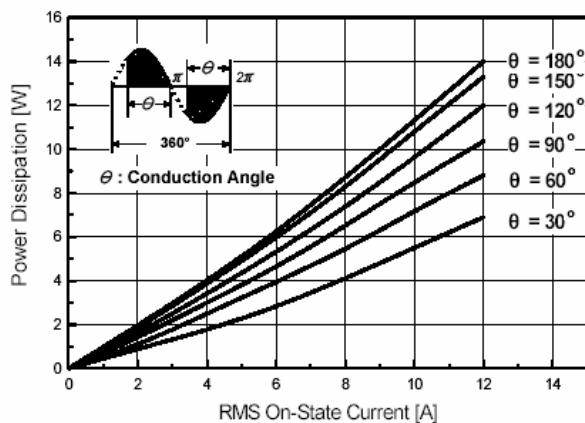
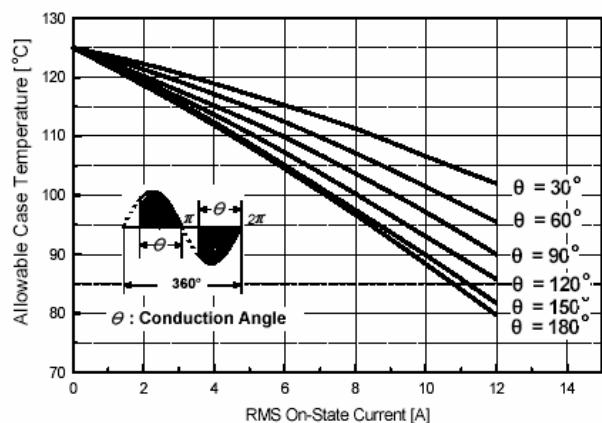
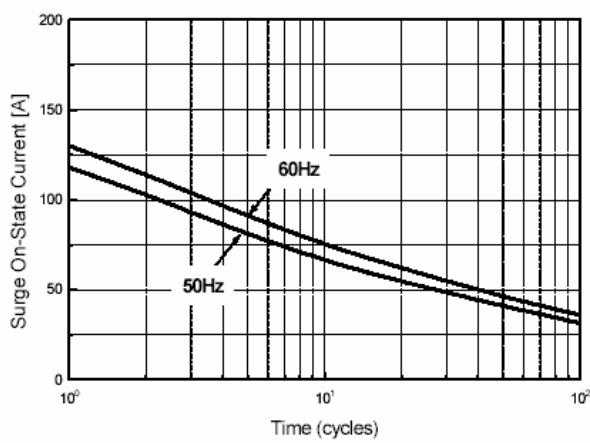
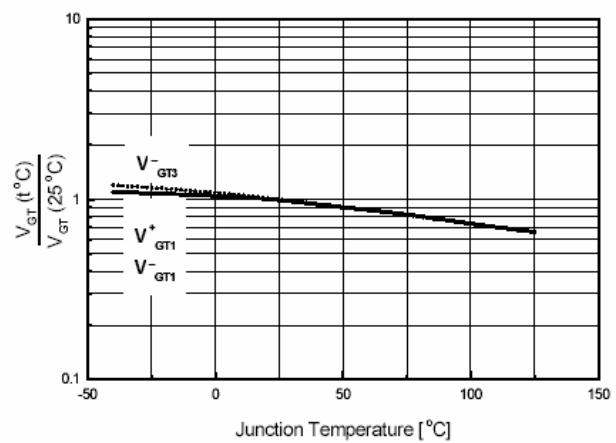
T_{stg} —Storage Temperature.....	-40~125
T_j —Operating Junction Temperature	-40~125
P_{GM} —Peak Gate Power Dissipation.....	5W
V_{DRM} —Repetitive Peak Off-State Voltage.....	600V
I_T (RMS)—R.M.S On-State Current ($T_a=79^\circ C$)	12A
V_{GM} —Peak Gate Voltage.....	10V
I_{GM} —Peak Gate Current.....	2.0A
I_{TSM} —Surge On-State Current (One Cycle, 50/60Hz,Peak,Non-Repetitive).....	119/130A
V_{ISO} —RMS Isolation Breakdown Voltage.....	2500V

Electrical Characteristics ($T_a=25^\circ C$)

Symbol	Items	Min.		Max.	Unit	Conditions
I_{DRM}	Repetitive Peak Off-State Current			2.0	mA	$V_D=V_{DRM}$, Single Phase,Half Wave, $T_J=125^\circ C$
V_{TM}	Peak On-State Voltage			1.4	V	$I_T=12A$, Inst. Measurement
I_{+GT1}	Gate Trigger Current ($+V_G$)			30	mA	$V_D=6V$, $R_L=10$ ohm
I_{-GT1}	Gate Trigger Current ($-V_G$)			30	mA	$V_D=6V$, $R_L=10$ ohm
I_{-GT3}	Gate Trigger Current ($-V_G$)			30	mA	$V_D=6V$, $R_L=10$ ohm
V_{+GT1}	Gate Trigger Voltage ($+V_G$)			1.5	V	$V_D=6V$, $R_L=10$ ohm
V_{-GT1}	Gate Trigger Voltage ($-V_G$)			1.5	V	$V_D=6V$, $R_L=10$ ohm
V_{-GT3}	Gate Trigger Voltage ($-V_G$)			1.5	V	$V_D=6V$, $R_L=10$ ohm
V_{GD}	Non-Trigger Gate Voltage	0.2			V	$T_J=125^\circ C$, $V_D=1/2V_{DRM}$
(dv/dt)c	Critical Rate of Rise of Off-State Voltage at Commutation	10			V/ μ s	$T_J=125^\circ C$, $VD=2/3VDRM$ (di/dt)c=-4.0A/ms
$R_{th(j-c)}$	Thermal Resistance			3.3	/W	Junction to case
I_H	Holding Current	20			mA	



Performance Curves

Fig 1. Gate Characteristics**Fig 2. On-State Voltage****Fig 3. On State Current vs.
Maximum Power Dissipation****Fig 4. On State Current vs.
Allowable Case Temperature****Fig 5. Surge On-State Current Rating
(Non-Repetitive)****Fig 6. Gate Trigger Voltage vs.
Junction Temperature**



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**Fig 7. Gate Trigger Current vs.
Junction Temperature**

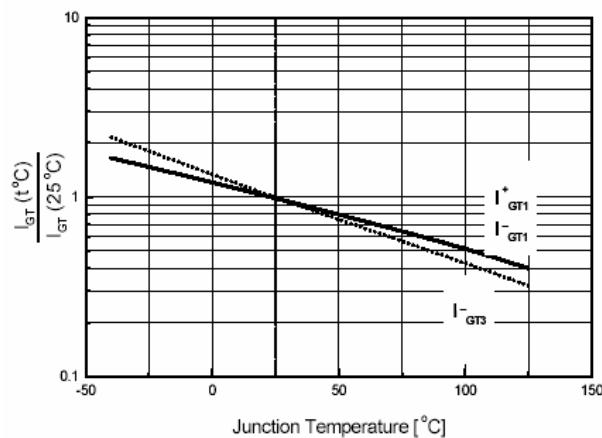


Fig 8. Transient Thermal Impedance

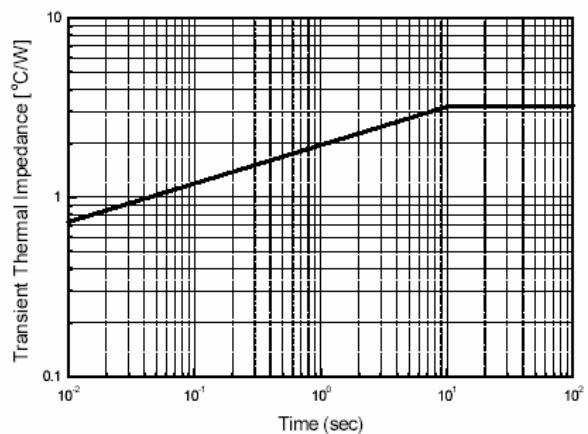


Fig 9. Gate Trigger Characteristics Test Circuit

